



7N65

Power MOSFET

7.4 Amps, 650 Volts N-CHANNEL POWER MOSFET

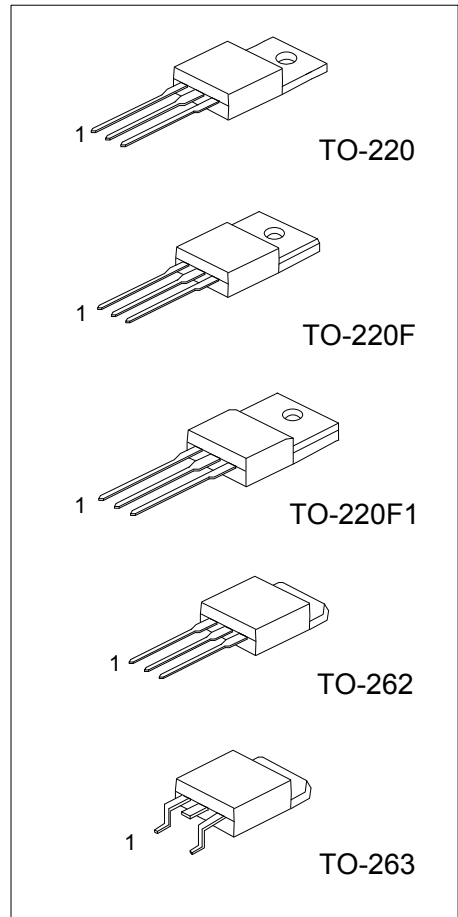
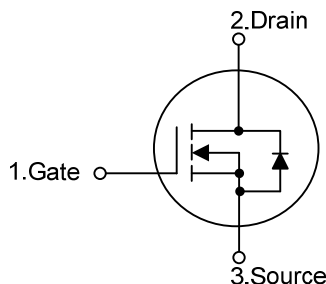
DESCRIPTION

The UTC **7N65** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} = 1.2\Omega$ @ $V_{GS} = 10V$
- * Ultra low gate charge (typical 29 nC)
- * Low reverse transfer Capacitance (C_{RSS} = typical 16pF)
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N65L-TA3-T	7N65G-TA3-T	TO-220	G	D	S	Tube
7N65L-TF1-T	7N65G-TF1-T	TO-220F1	G	D	S	Tube
7N65L-TF3-T	7N65G-TF3-T	TO-220F	G	D	S	Tube
7N65L-T2Q-T	7N65G-T2Q-T	TO-262	G	D	S	Tube
7N65L-TQ2-R	7N65G-TQ2-R	TO-263	G	D	S	Tape Reel
7N65L-TQ2-T	7N65G-TQ2-T	TO-263	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

7N65L-TA3-T (1) Packing Type (2) Package Type (3) Lead Plating	(1) R: Tape Reel, T: Tube (2) TA3: TO-220, TF1: TO220-F1, TF3: TO-220F T2Q: TO-262, TQ2: TO-263 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	7.4	A
Drain Current	Continuous	I_D	7.4	A
	Pulsed (Note 2)	I_{DM}	29.6	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	530	mJ
	Repetitive (Note 2)	E_{AR}	14.2	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262/TO-263	P_D	142	W
	TO-220F/TO-220F1		48	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L = 19.5\text{mH}$, $I_{AS} = 7.4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 7.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-262/TO-263	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	0.88	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.6	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Drain-Source Leakage Current		I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS} / \Delta T_J$	$I_D = 250\mu A$, Referenced to 25°C		0.67		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.7A$			1.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{ MHz}$			1400	pF
Output Capacitance		C_{OSS}				180	pF
Reverse Transfer Capacitance		C_{RSS}			16	21	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	$V_{DD} = 300V, I_D = 7.4A, R_G = 25\Omega$ (Note 1, 2)			70	ns
Turn-On Rise Time		t_R				170	ns
Turn-Off Delay Time		$t_{D(OFF)}$				140	ns
Turn-Off Fall Time		t_F				130	ns
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	$V_{DS}=480V, I_D=7.4A, V_{GS}=10\text{ V}$ (Note 1, 2)		29	38	nC
Gate-Source Charge		Q_{GS}			7		nC
Gate-Drain Charge		Q_{GD}			14.5		nC

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 7.4 A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				7.4	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				29.6	A
Reverse Recovery Time	t_{RR}	$V_{GS} = 0V, I_S = 7.4 A,$		320		ns
Reverse Recovery Charge	Q_{RR}	$dI_F / dt = 100A/\mu s$ (Note 1)		2.4		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
 2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

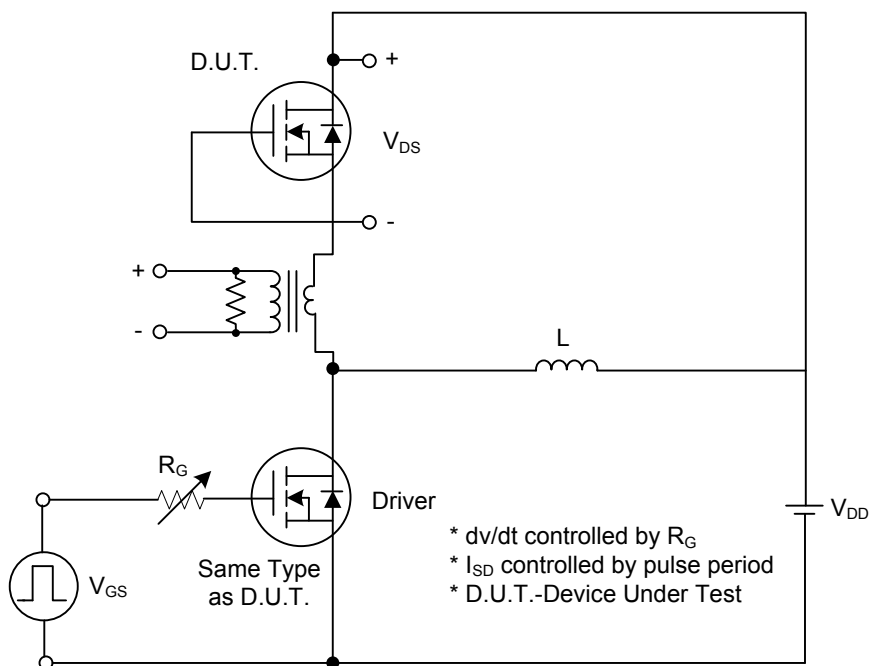


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

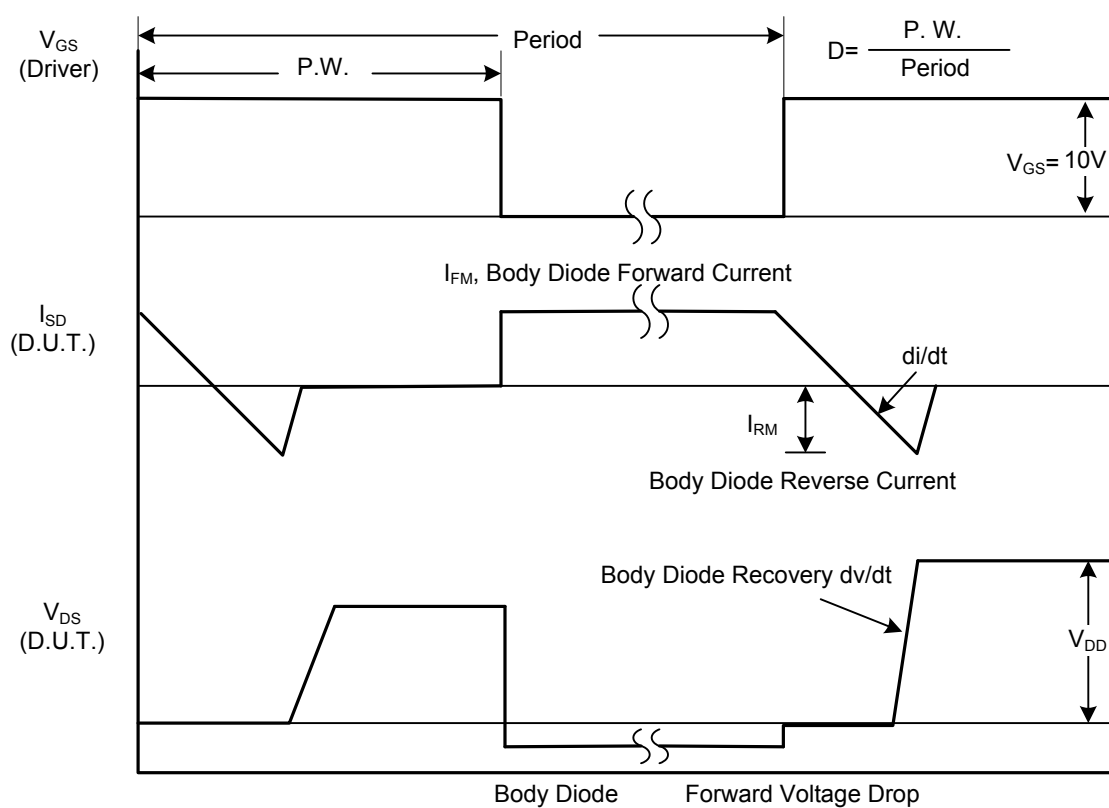


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

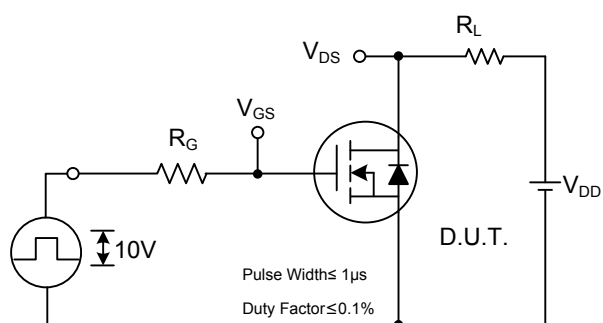


Fig. 2A Switching Test Circuit

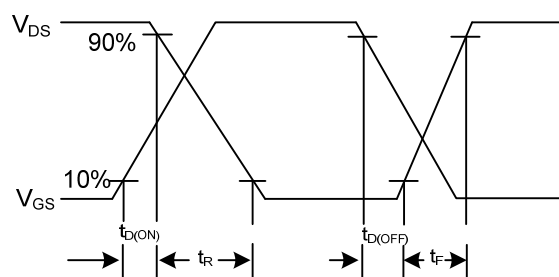


Fig. 2B Switching Waveforms

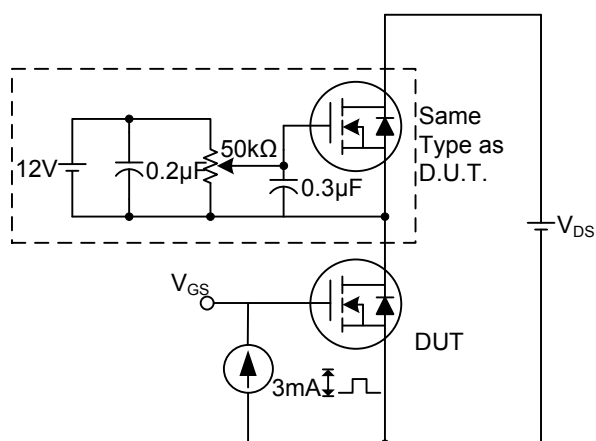


Fig. 3A Gate Charge Test Circuit

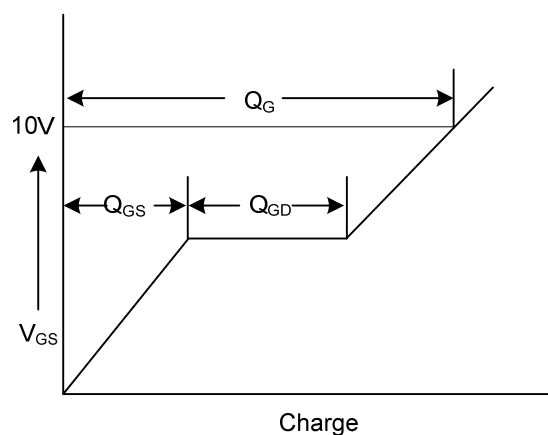


Fig. 3B Gate Charge Waveform

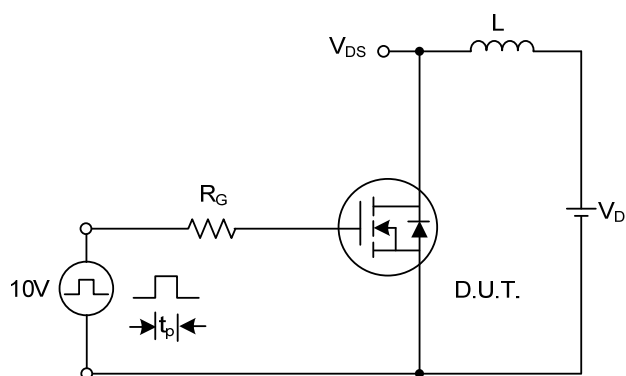


Fig. 4A Unclamped Inductive Switching Test Circuit

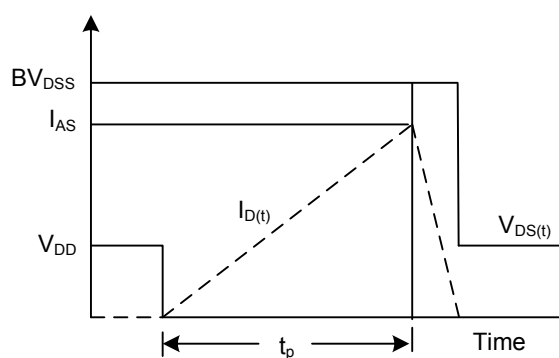


Fig. 4B Unclamped Inductive Switching Waveforms

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